

IN THE CLAIMS:

1. (Previously Presented) A semiconductor component, comprising a semiconductor element encased by a cover element having an integrated electroconductive element comprising at least one outlet, wherein the at least one outlet is configured to connect the electroconductive element to ground in order to shield the semiconductor element against electrostatic pulses.
2. (Original) A semiconductor component according to claim 1, wherein in structure, the electroconductive element is a planar sheet.
3. (Original) A semiconductor component according to claim 1, wherein the electroconductive element is a thin loop structure.
4. (Original) A semiconductor component according to claim 1, wherein the electroconductive element forms a permanent, integrated part of the semiconductor component.
5. (Previously Presented) A semiconductor component according to claim 1, wherein the electroconductive element is placed underneath the cover element of the semiconductor component, inside said cover element.
6. (Previously Presented) A semiconductor component according to claim 1, wherein the electroconductive element is attached to the cover element of the semiconductor component, outside said cover element.
7. (Original) A semiconductor component according to claim 1, wherein the electroconductive element is induced in the cover element of the semiconductor component either chemically or electrochemically.
8. (Previously Presented) A method for shielding a semiconductor element against electrostatic pulses, comprising: integrating the semiconductor element in a semiconductor component, covering the semiconductor element with a cover element, integrating an electroconductive element within the cover element of the semiconductor component and providing at least one outlet for the integrated

electroconductive element, so that the at least one outlet is configured to connect the electroconductive element to ground.

9. (Original) A method according to claim 8, wherein in the semiconductor component, there is integrated an electroconductive, planar element.

10. (Original) A method according to claim 8, wherein in the semiconductor component, there is integrated an electroconductive, loop-shaped element.

11. (Previously Presented) A method according to claim 8, wherein the electroconductive element is integrated as a permanent part of the semiconductor component.

12. (Currently Amended) A method according to claim 11, wherein the electroconductive element is integratedplaced underneath the cover element of the semiconductor component, inside said cover element.

13. (Currently Amended) A method according to claim 11, wherein the electroconductive element is integratedby attachmentattached to the cover element of the semiconductor component, outside said cover element.

14. (Original) A method according to claim 8, wherein the electroconductive element is induced in the cover element of the semiconductor component either chemically or electrochemically.

15. (Previously Presented) An arrangement including a mounting tray and at least one semiconductor component, wherein said at least one semiconductor component comprises a semiconductor element encased by a cover element having an integrated electroconductive element, where the electroconductive element is provided with at least one outlet that is grounded to a ground plane of the mounting tray.

16. (Previously Presented) Apparatus for shielding a semiconductor element against electrostatic pulses, comprising:

means for covering the semiconductor element in a semiconductor component having an integrated electroconductive element; and

means for providing at least one outlet for the integrated electroconductive element, so that the at least one outlet is configured to connect the electroconductive element to ground.

17. (Previously Presented) The apparatus of claim 16, wherein in the semiconductor component, there is integrated an electroconductive, planar element.

18. (Previously Presented) The apparatus of claim 16, wherein in the semiconductor component, there is integrated an electroconductive, loop-shaped element.

19. (Previously Presented) The apparatus of claim 16, wherein the electroconductive element is integrated as a permanent part of the semiconductor component.

20. (Previously Presented) The apparatus of claim 16, wherein the electroconductive element is integrated underneath the means for covering the semiconductor component, inside said cover element.